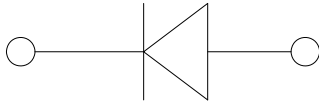
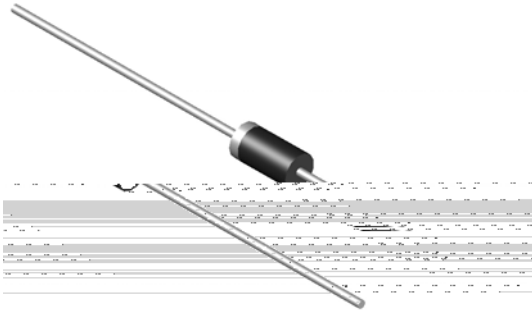




HER151-158



- High efficiency
- High current capability
- High Reliability
- High surge current capability
- Glass passivated chip junction
- Solder dip 275 °C max. 7 s, per JESD 22-B106

- DO-204AC (DO-15)
- Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant
- Tin plated leads, solderable per J-STD-002 and JESD22-B102
- Color band denotes cathode end

Electrical Characteristics (Ta=25 °C) Unless otherwise specified

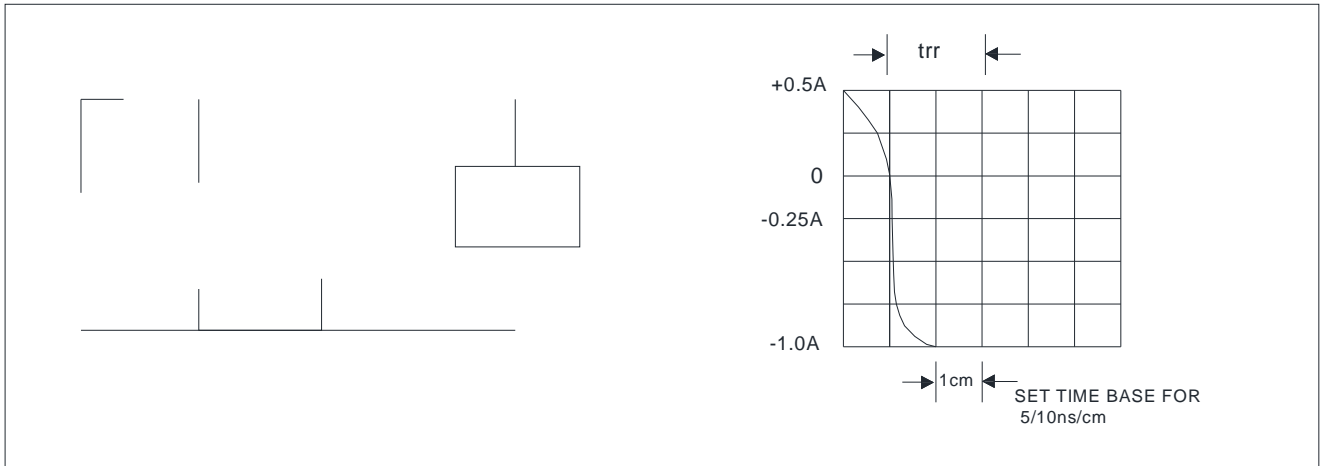
Parameter	Symbol	Unit	HER151 G	HER152 G	HER153 G	HER154 G	HER155 G	HER156 G	HER157 G	HER158 G
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	V	50	100	200	300	400	600	800	1000
Maximum RMS Voltage	V_{RMS}	V	35	70	140	210	280	420	560	700
Average Forward Current @60Hz sine wave, Resistance load, Ta=75	$I_{F(AV)}$	A	1.5							
Forward Surge Current (Non-repetitive) @60Hz Half-sine wave, 1 cycle, Tj=25	I_{FSM}	A	60							
Forward Surge Current (Non-repetitive) @1ms, square wave, 1 cycle, Tj=25			100							
Current squared time @1ms t8.3 ms Tj=25 Rating of per diode	I^2t	A ² s	15							
Typical junction capacitance @Measured at 1MHz and Applied Reverse Voltage of 4.0 V.D.C	C_j	pF	28			17		12		
Storage Temperature	T_{stg}		-55 ~ +150							
Junction Temperature	T_j		-55 ~ +150							

Electrical Characteristics (Ta=25 °C) Unless otherwise specified

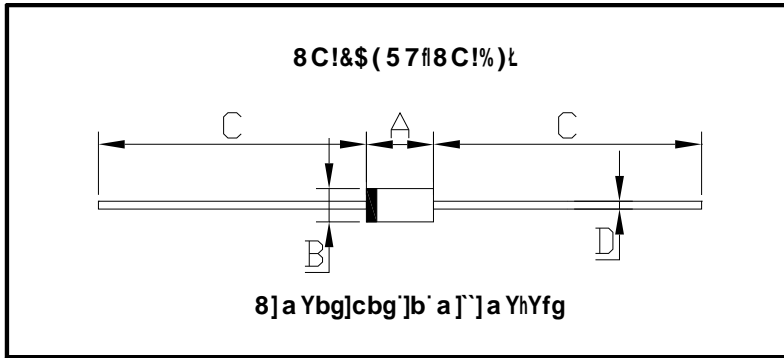
Parameter	Symbol	Unit	HER151-158
Maximum instantaneous forward voltage drop per diode	V_F	V	$I_{FM}=1.5A$ 1.0
Maximum DC reverse current at rated DC blocking voltage per diode	I_R	μA	$T_j=25$ 2.5
			$T_j=125$ 100
Maximum reverse recovery time	t_{rr}	ns	$I_F=0.5A, I_R=1.0A, I_r=0.25A$ 50



:: ; ') . 8]U[fUa 'cZ'W]fWi]h'UbX'HYgh]b[' kUjY'Zcfa 'cZ'fYjYfgY'fYWc jYfm'h]a Y



C i h`]bY`8] a Ybg]cbg`



8C!&\$ (57f!8C!%)L`		
Dim	Min	Max
A	5.80	7.60
B	2.60	3.60
C	25.4	/
D	0.70	0.90

